



## Bridge Rectifier

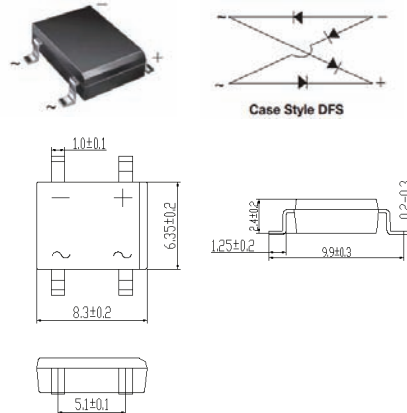
### ■ Features

- $I_o$  1.5A
- $V_{RRM}$  50V~1000V
- Glass passivated chip

### ■ Applications

- General purpose 1 phase Bridge rectifier applications

### ■ Outline Dimensions and Mark



### ■ Limiting Values (Absolute Maximum Rating)

Item	Symbol	Unit	Conditions	DF15						
				005S	01S	02S	04S	06S	08S	10S
Repetitive Peak Reverse Voltage	$V_{RRM}$	V		50	100	200	400	600	800	1000
Average Rectified Output Current	$I_o$	A	$T_a=25^\circ\text{C}$ 60Hz sine wave, R-load, $T_a=25^\circ\text{C}$ On glass-epoxi substrate	1.5						
Surge(Non-repetitive)Forward Current	$I_{FSM}$	A	60Hz sine wave, 1 cycle, $T_j=25^\circ\text{C}$	50						
Current Squared Time	$I^2t$	$\text{A}^2\text{S}$	$1\text{ms} \leq t < 8.3\text{ms}$ $T_j=25^\circ\text{C}$ , Rating of per diode	11						
Storage Temperature	$T_{stg}$	$^\circ\text{C}$		-55 ~+150						
Junction Temperature	$T_j$	$^\circ\text{C}$		-55 ~+150						

### ■ Electrical Characteristics ( $T_a=25^\circ\text{C}$ Unless otherwise specified)

Item	Symbol	Unit	Test Condition	Max
Peak Forward Voltage	$V_{FM}$	V	$I_{FM}=1.5\text{A}$ , Pulse measurement, Rating of per diode	1.1
Peak Reverse Current	$I_{RRM}$	$\mu\text{A}$	$V_{RM}=V_{RRM}$ , Pulse measurement, Rating of per diode	10
Thermal Resistance	$R_{\theta J-A}$	$^\circ\text{C}/\text{W}$	Between junction and ambient, On glass-epoxi substrate	68
	$R_{\theta J-L}$		Between junction and lead	15



### ■ Characteristics(Typical)

FIG1:Io-TaCurve

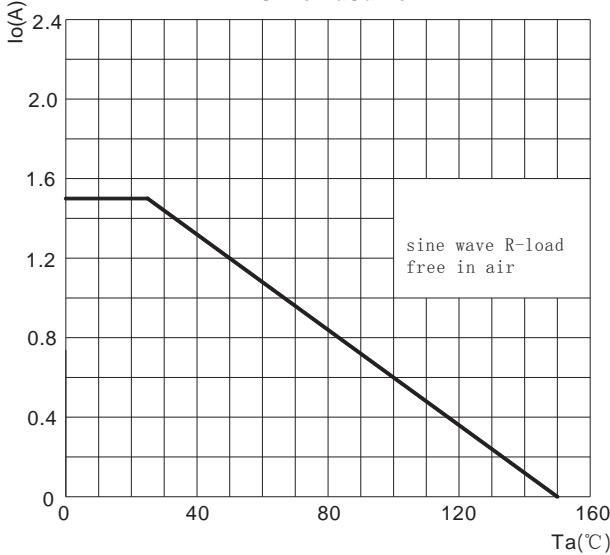


FIG2:Surge Forward Current Capadility

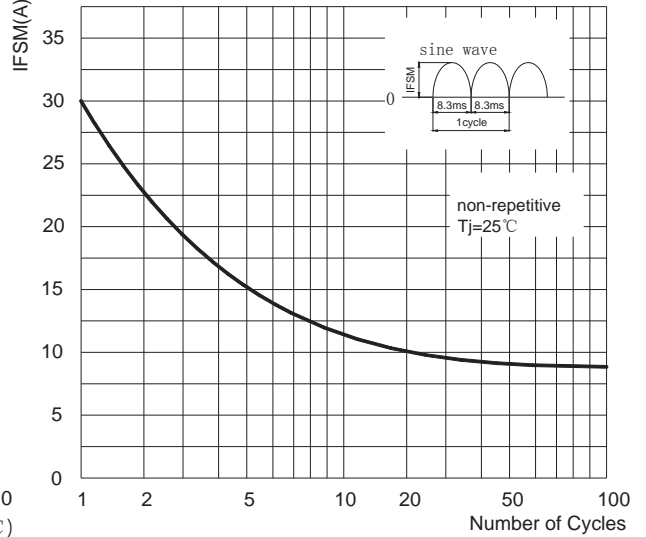


FIG3: Forward Voltage

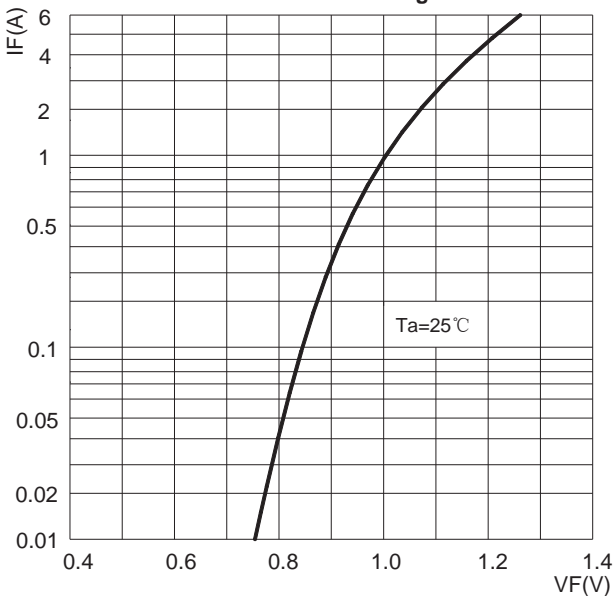


FIG4:Typical Reverse Characteristics

